

SANYO Semiconductors DATA SHEET

2SC4521 — NPN Epitaxial Planar Silicon Transistor High-Speed Switching Applications

Features

- · Adoption of FBET, MBIT processes.
- · Large current capacity.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- · Small-sized package.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		60	V
Collector-to-Emitter Voltage	VCEO		45	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		3	А
Collector Current (Pulse)	ICP		6	А
Collector Dissipation	PC	Mounted on a ceramic board (250mm ² X0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =45V, I _E =0A			1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =2V, I _C =0A			10	μΑ

Marking: CL Continued on next page.

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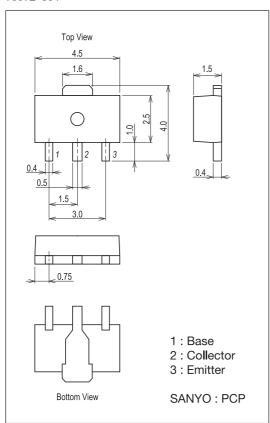
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Offic	
DC Current Gain	hFE1	VCE=2V, IC=500mA	100*		400*		
	hFE2	V _{CE} =2V, I _C =3A	40				
Gain-Bandwidth Product	fT	V _{CE} =2V, I _C =500mA		300		MHz	
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		25		pF	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =1.5A, I _B =75mA		0.25	0.7	V	
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =1.5A, I _B =75mA		0.95	1.3	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0A	60			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	45			V	
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =100μA, I _C =0A	5			V	
Turn-ON Time	ton	See specified Test Circuit.		50	100	ns	
Storage Time	tstg	See specified Test Circuit.		150	270	ns	
Turn-OFF Time	toff	See specified Test Circuit.		180	350	ns	

^{*:} The 2SC4521 is classified by 500mA hFE as follows:

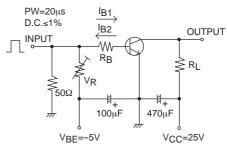
Rank	R	S	T	
hFE	100 to 200	140 to 280	200 to 400	

Package Dimensions

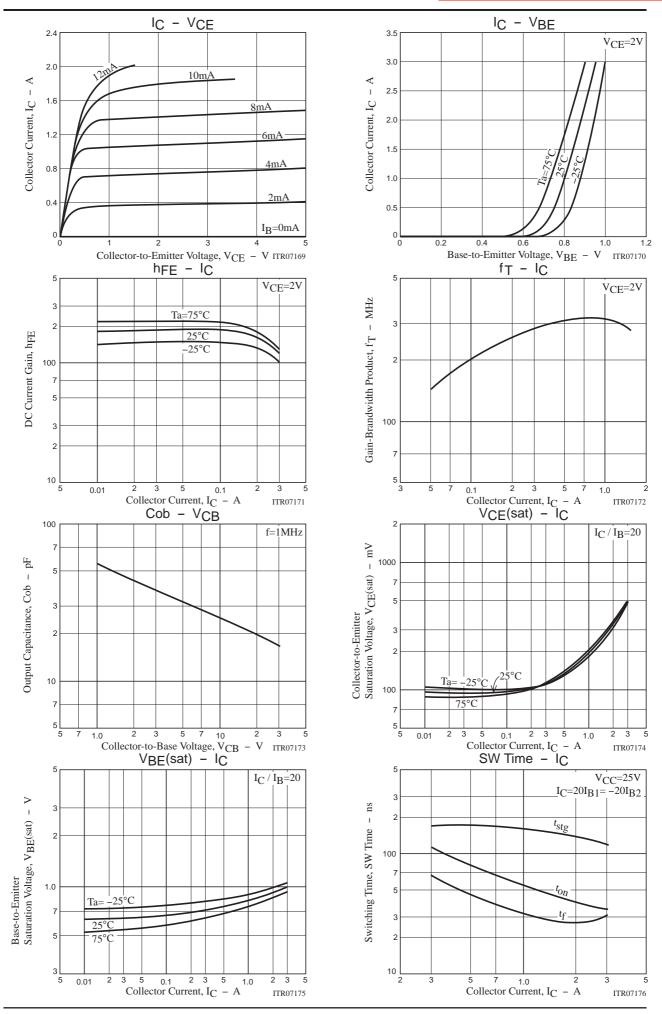
unit : mm (typ) 7007B-004

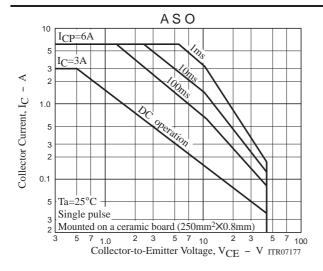


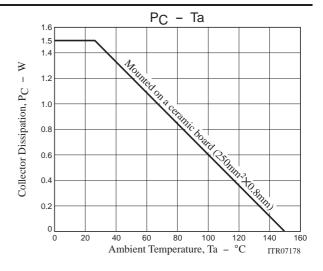
Switching Time Test Circuit



IC=20IB1=-20IB2=1.5A







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